



SOT-23 Plastic-Encapsulate Transistors

MMBT2907ALT1 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.3 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

$$I_{CM}: -0.6 \text{ A}$$

Collector-base voltage

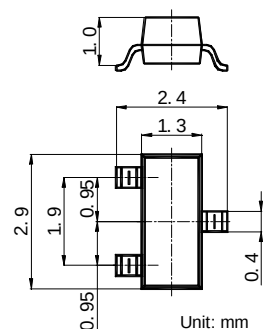
$$V_{(BR)CBO}: -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}$, $I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 \text{ mA}$, $I_B = 0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}$, $I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB} = -3\text{V}$, $I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}$, $I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10\text{V}$, $I_C = -150\text{mA}$	100		300	
	$h_{FE(2)}$	$V_{CE} = -10\text{V}$, $I_C = -1\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}$, $I_B = -50 \text{ mA}$			-1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}$, $I_B = -50 \text{ mA}$			-2	V
Transition frequency	f_T	$V_{CE} = -20\text{V}$, $I_C = -50\text{mA}$ $f = 100\text{MHz}$	200			MHz

DEVICE MARKING:

MMBT2907ALT1 =2F